

Silicon PNP Power Transistor

2SB1455

DESCRIPTION

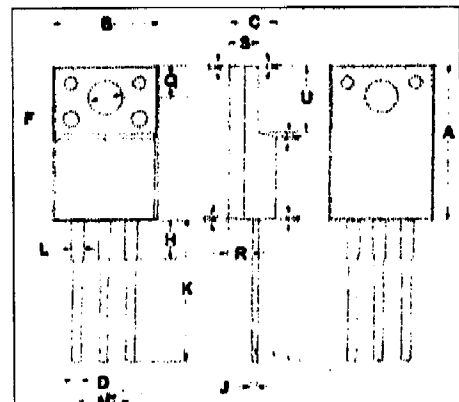
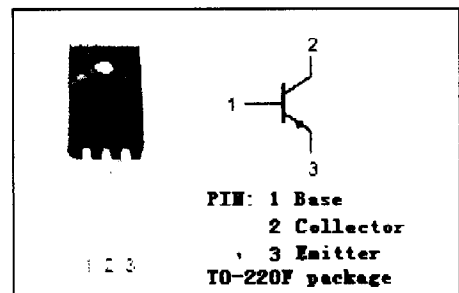
- Collector-Emitter Breakdown Voltage-
 : $V_{(BR)CEO} = -80V(\text{Min})$
- Low Collector Saturation Voltage-
 : $V_{CE(sat)} = -0.5V(\text{Max}) @ (I_C = -4A, I_B = -0.4A)$
- Complement to Type 2SD2203

APPLICATIONS

- Designed for high-current switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-90	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Pulse	-12	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	30	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; R _{BE} = ∞	-80			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA; I _E = 0	-90			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -4A; I _B = -0.4A			-0.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -80V; I _E = 0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-100	μ A
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -2V	70		280	
h _{FE-2}	DC Current Gain	I _C = -4A; V _{CE} = -2V	30			
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -5V		20		MHz

Switching Times

t _{on}	Turn-on Time	V _{CC} = -50V, R _L = 25Ω, I _C = -2A; I _{B1} = -I _{B2} = -0.2A,		0.2		μ s
t _{stg}	Storage Time			0.7		μ s
t _r	Fall Time			0.2		μ s

◆ h_{FE-1} Classifications

Q	R	S
70-140	100-200	140-280